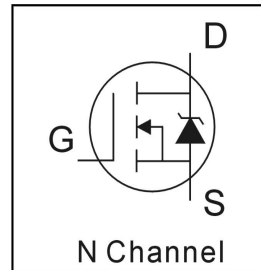


**N Channel Power MOSFET FOR LOGIC DRIVER**

**Chip Specification**

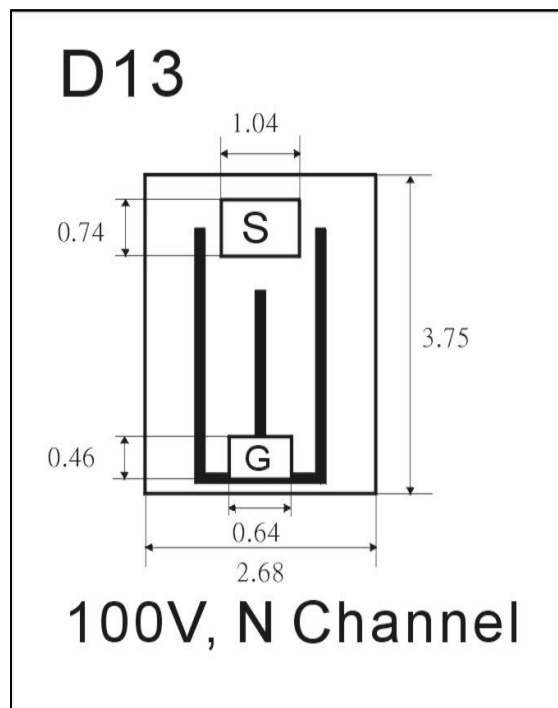
**General Description:**

- \* Advanced Process Technology
- \* Dynamic dv/dt Rating
- \* **175°C Operating Temperature**
- \* **Fast Switching**
- \* **Fully Avalanche Rated**
- \* **RDS(ON) rated at VGS = 5V**
- \* **Ease of parallel**



**Mechanical Data:**

<b>D13</b>	
Dimension	<b>2.68mm x 3.75mm</b>
Thickness:	<b>400 μm</b>
Metallization:	
Top :	<b>Al</b>
Backside :	<b>CrNiAg / Au</b>
Suggested Bonding Conditions:	
Die Mounting:	<b>Solder Perform</b>
<b>95/5 PbSn or 92.5./2.5/5 PbAgIn</b>	
Source Bonding Wire: <b>10 mil Al</b>	



**Absolute Maximum Rating**

@Ta=25°C

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	100	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	0.16	Ω	VGS=5V, ID=9A
Continuous Drain current ( in target package)	ID@25°C	15	A	VGS= 5V
Continuous Drain current ( in target package)	ID@100°C	11	A	VGS= 5V
Operation Junction Temperature	Tj	-55~175	°C	
Storage Temperature	TSTR	-55~175	°C	

**Target Device: IRL530**

TO-220AB

Pd

88

W

@Tc=25°C

